

ABSTRACT OF THE DISCLOSURE

A semiconductor device having a gate and a fabrication method therefor is disclosed, which can improve a thermal stability, has a low resistance, and assure an easy fabrication process. The fabrication method includes the steps of (1) forming a first insulating film and a conductive film on a semiconductor substrate, (2) patterning the first insulating film and a conductive film on a semiconductor substrate, (2) patterning the first insulating film and the conductive film, to form a gate, (3) forming a second insulating film thicker than the gate on an entire surface, (4) planarizing the second insulating film, to expose the gate, (5) depositing a refractory metal layer on an entire surface, (6) forming a silicide layer on an upper surface of the gate by heat treatment, and (7) etching the refractory metal layer and the second insulating film.